

# MCR1718

High-reliability discrete products and engineering services since 1977

### SILICON CONTROLLED RECTIFIER

#### FEATURES

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
- Available as non-RoHS (Sn/Pb plating), standard, and as RoHS by adding "-PBF" suffix.

### MAXIMUM RATINGS

Rating	Symbol	Value	Unit	
Peak Reverse Blocking Voltage (1)				
MCR1718-5		300		
MCR1718-6	V <sub>RRM</sub>	400	Volts	
MCR1718-7		500		
MCR1718-8		600		
Non-Repetitive Peak Reverse Voltage				
(Transient, Non-recurrent 5 ms(max)				
MCR1718-5		400	Volts	
MCR1718-6	V <sub>RSM</sub>	500		
MCR1718-7		600		
MCR1718-8		700		
Forward Current RMS	I <sub>T(RMS)</sub>	25	Amp	
Peak Forward Surge Current		1000	Amp	
(1-10 μs Pulse Width)	I <sub>TSM</sub>	1000		
Current Application Rate	-1: / -1+	1000	A /	
(up to 1000 Adc peak)	di/dt	1000	A/µs	
Circuit Fusing Considerations	l <sup>2</sup> t	250	A <sup>2</sup> s	
(T <sub>J</sub> = -65 to +125°C; t ≤ 1.0 ms)	It	250	A s	
Dynamic Average Power		20	\\/_\\_	
(T <sub>c</sub> = 65°C)	P <sub>F(AV)</sub>	30	Watts	
Peak Gate Power –Forward	P <sub>GM</sub>	20	Watts	
Average Gate Power – Forward	P <sub>G(AV)</sub>	1.0	Watt	
Peak Gate Current – Forward	I <sub>GM</sub>	5.0	Amp	
Peak Gate Voltage	V <sub>GM</sub>	10	Volts	
Operating Junction Temperature Range	TJ	-65 to +125	°C	
Storage Temperature Range	T <sub>stg</sub>	-65 to +150	°C	
Stud Torque	-	30	Inlb	

Note 1: V<sub>RRM</sub> for all types can be applied on a continuous dc basis without incurring damage. Ratings apply for zero or negative gate voltage.

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	R <sub>θJC</sub>	2.0	°C/W



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### **ELECTRICAL CHARACTERISTICS** (T<sub>c</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min.	Тур.	Max.	Units
Peak Forward Blocking Voltage (2)					
(T <sub>J</sub> = 125°C)					
MCR1718-5		300	-	-	Volts
MCR1718-6	V <sub>DRM</sub>	400	-	-	Voits
MCR1718-7		500	-	-	
MCR1718-8		600	-	-	
Peak Forward Blocking Current					
(Rated $V_{DRM}$ with gate open, $T_J = 125^{\circ}C$ )	I <sub>DRM</sub>	-	-	8.0	mA
Peak Reverse Blocking Current					mA
(Rated $V_{RRM}$ with gate open, $T_J = 125^{\circ}C$ )	I <sub>RRM</sub>	-	-	8.0	
Forward "on" Voltage					
(I <sub>F</sub> = 25 Adc)		-	1.1	1.3	
(I <sub>GT</sub> = 500 mA, I <sub>pulse</sub> = 500 Amps)	V <sub>TM</sub>				Volts
(1µs after start (10% pt.) of I <sub>pulse</sub> )		-	0.30	-	
(5.0µs after start (10% pt.) of I <sub>pulse</sub> )		-	5.0	-	
Gate Trigger Current (Continuous dc)	I <sub>GT</sub>				mA
(Anode Voltage = 7.0 Vdc, R <sub>L</sub> = 50 Ohms)		-	10	50	
Gate Trigger Voltage (Continuous dc)					Volts
(Anode Voltage = 7.0 Vdc, R <sub>L</sub> = 50 Ohms)	V <sub>GT</sub>	-	0.8	1.5	
(Anode Voltage = Rated $V_{DRM}$ , $R_L$ = 500 Ohms,		0.25	-	-	
T <sub>J</sub> = 125°C)	V <sub>GD</sub>				
Holding Current	I <sub>H</sub>				mA
(Anode Voltage = 7.0 Vdc, Gate Open)		5.0	15	-	
(Anode Voltage = 7.0 Vdc, Gate Open, T <sub>J</sub> =		-	6.0	-	
125°C)					
Circuit Commutated Turn-Off Time	t <sub>q</sub>				μs
(I <sub>F</sub> = 500 A, I <sub>R</sub> = 10A, dv/dt = 20 V/µs)		-	20	-	
(Conductive Charging Circuit – Circuit dependent)					
Critical Exponential Rate of Rise	dv/dt				V/µs
(Gate Open, T」= 125°C)		-	100	-	

Note 2: V<sub>DRM</sub> for all types can be supplied on a continuous basis without incurring damage. Ratings apply for zero or negative gate voltage.



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#### MECHANICAL CHARACTERISTICS

Case	TO-48	
Marking	Body painted, alpha-numeric	
Polarity	Cathode is stud	



	TO-48			
	Inches		Millin	neters
	Min	Max	Min	Max
CD	1	0.543	8	13.793
СН		0.550	-	13.970
HF	0.544	0.563	13.817	14.301
OAH	3	1.193		30.303
SL	0.422	0.453	10.718	11.507
ΦT	0.125	0.165	3.175	4.191
ΦT <sub>1</sub>	0.060	0.075	1.524	1.905